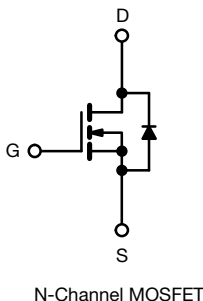
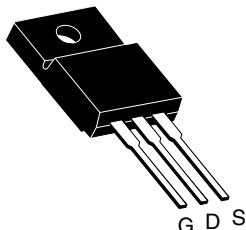


## D Series Power MOSFET

**TO-220 FULLPAK**


N-Channel MOSFET

### FEATURES

- Optimal design
  - Low area specific on-resistance
  - Low input capacitance ( $C_{iss}$ )
  - Reduced capacitive switching losses
  - High body diode ruggedness
  - Avalanche energy rated (UIS)
- Optimal efficiency and operation
  - Low cost
  - Simple gate drive circuitry
  - Low figure-of-merit (FOM):  $R_{on} \times Q_g$
  - Fast switching
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS\***  
Available

### Note

\* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

### APPLICATIONS

- Consumer electronics
  - Displays (LCD or Plasma TV)
- Server and telecom power supplies
  - SMPS
- Industrial
  - Welding
  - Induction heating
  - Motor drives
- Battery chargers

### PRODUCT SUMMARY

$V_{DS}$ (V) at $T_J$ max.	550	
$R_{DS(on)}$ max. ( $\Omega$ ) at 25 °C	$V_{GS} = 10$ V	0.28
$Q_g$ max. (nC)	76	
$Q_{gs}$ (nC)	11	
$Q_{gd}$ (nC)	17	
Configuration	Single	

### ORDERING INFORMATION

Package	TO-220 FULLPAK
Lead (Pb)-free	SiHF18N50D-E3

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	$V_{DS}$	500	V
Gate-source voltage	$V_{GS}$	$\pm 30$	
Gate-source voltage AC ( $f > 1$ Hz)		30	
Continuous drain current ( $T_J = 150$ °C) <sup>e</sup>	$V_{GS}$ at 10 V	$T_C = 25$ °C	A
		$T_C = 100$ °C	
Pulsed drain current <sup>a</sup>	$I_{DM}$	53	
Linear derating factor		0.3	W/°C
Single pulse avalanche energy <sup>b</sup>	$E_{AS}$	115	mJ
Maximum power dissipation	$P_D$	39	W
Operating junction and storage temperature range		$T_J, T_{stg}$	-55 to +150 °C
Drain-source voltage slope	$dV/dt$	$T_J = 125$ °C	V/ns
Reverse diode $dV/dt$ <sup>d</sup>			
Soldering recommendations (peak temperature) <sup>c</sup>		For 10 s	°C
Mounting torque		M3 screw	Nm


### Notes

- Repetitive rating; pulse width limited by maximum junction temperature
- $V_{DD} = 50$  V, starting  $T_J = 25$  °C,  $L = 2.3$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 10$  A
- 1.6 mm from case
- $I_{SD} \leq I_D$ , starting  $T_J = 25$  °C
- Limited by maximum junction temperature

**THERMAL RESISTANCE RATINGS**

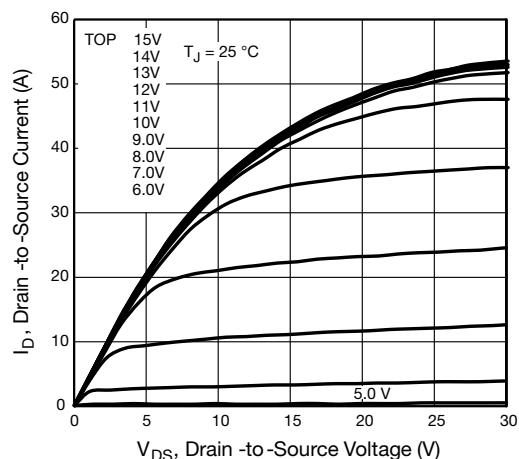
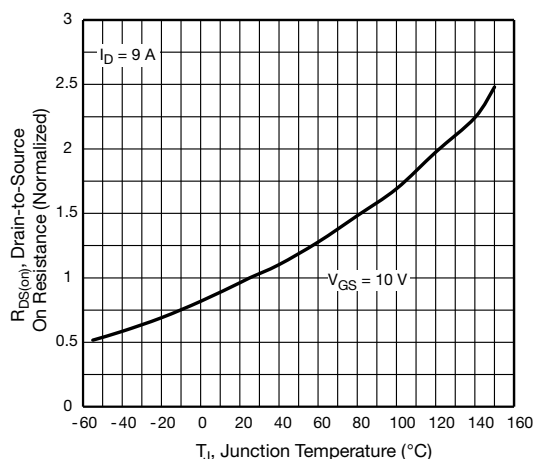
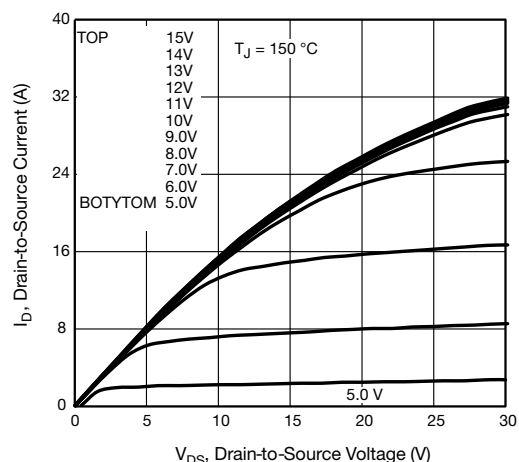
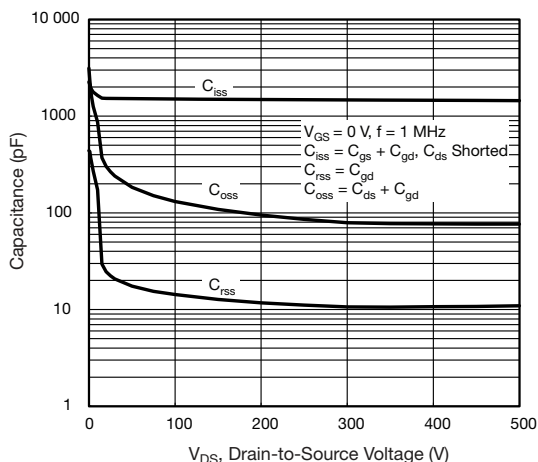
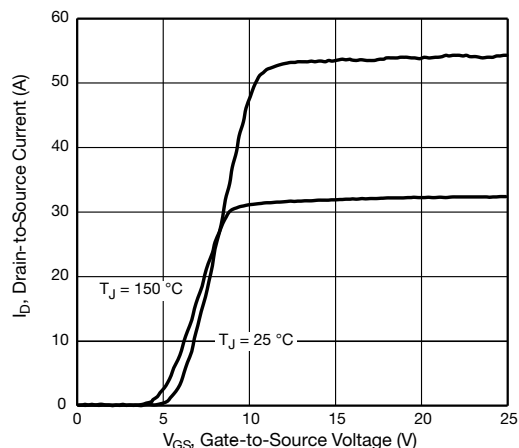
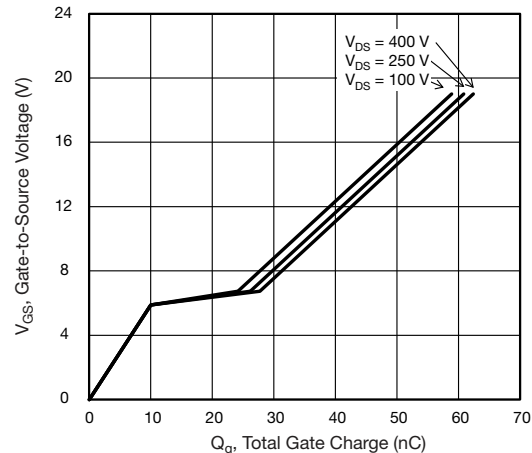
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	$R_{thJA}$	-	65	°C/W
Maximum junction-to-case (drain)	$R_{thJC}$	-	3.2	

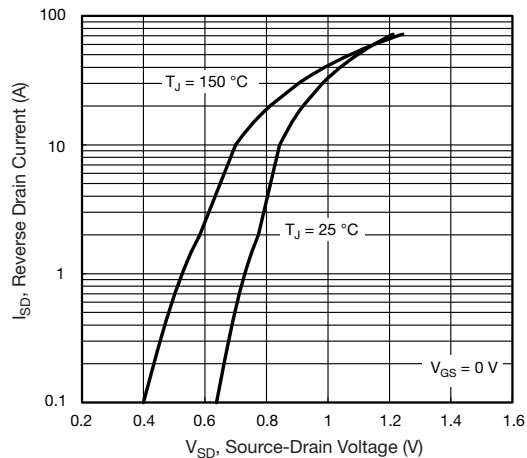
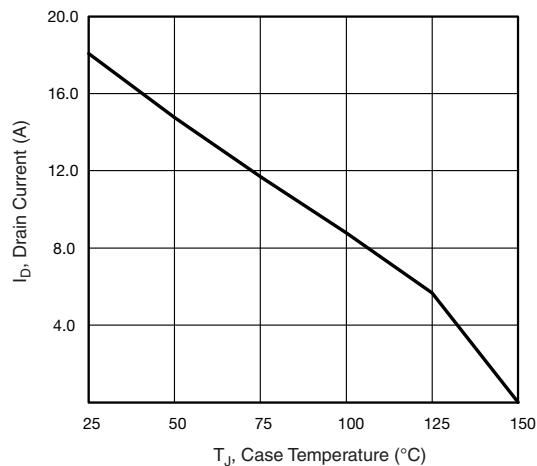
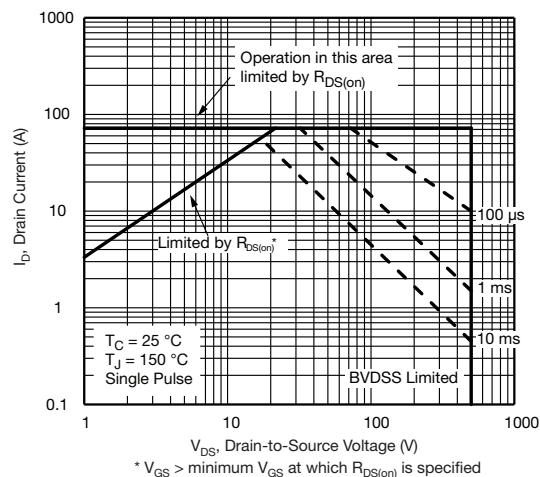
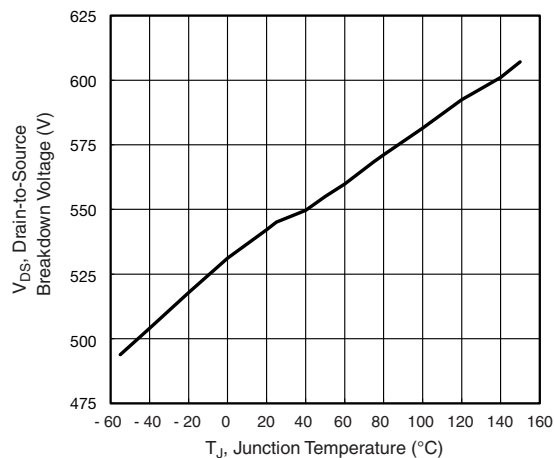
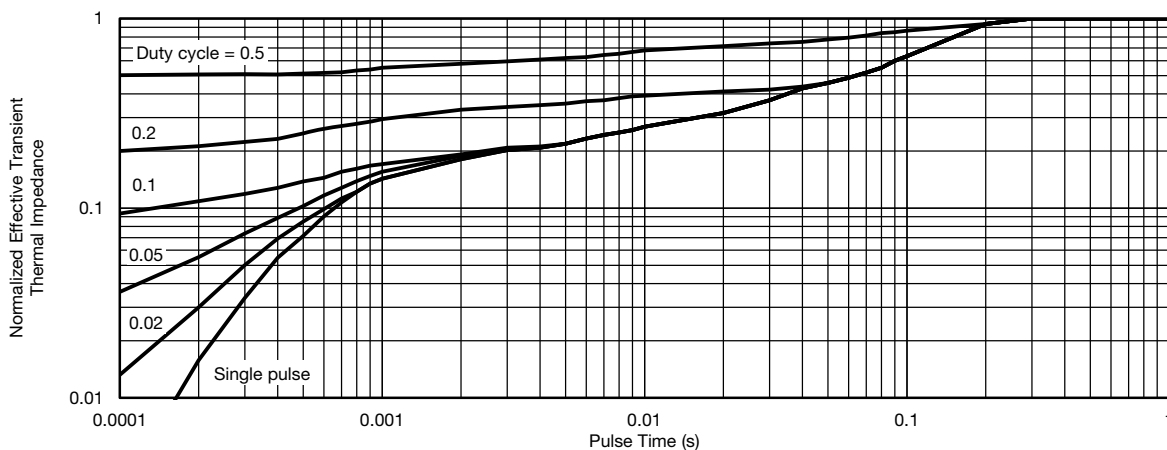
**SPECIFICATIONS** ( $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

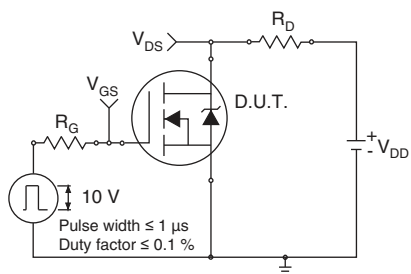
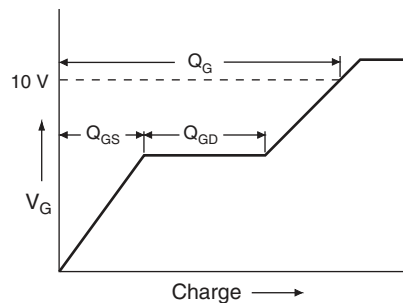
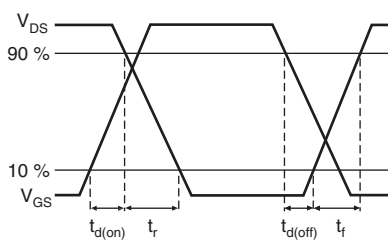
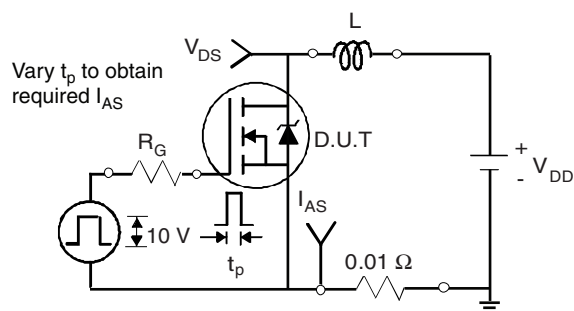
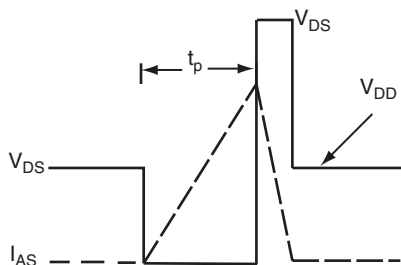
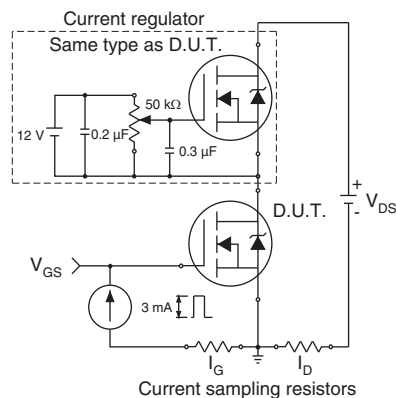
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$	500	-	-	V
$V_{DS}$ temperature coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^{\circ}\text{C}$ , $I_D = 250\text{ }\mu\text{A}$	-	0.58	-	V/ $^{\circ}\text{C}$
Gate threshold voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	3.0	-	5.0	V
Gate-source leakage	$I_{GSS}$	$V_{GS} = \pm 30\text{ V}$	-	-	$\pm 100$	nA
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 500\text{ V}$ , $V_{GS} = 0\text{ V}$	-	-	1	$\mu\text{A}$
		$V_{DS} = 400\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 125\text{ }^{\circ}\text{C}$	-	-	10	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ , $I_D = 9\text{ A}$	-	0.23	0.28	$\Omega$
Forward transconductance	$g_{fs}$	$V_{DS} = 50\text{ V}$ , $I_D = 9\text{ A}$	-	6.4	-	S
<b>Dynamic</b>						
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = 100\text{ V}$ , $f = 1.0\text{ MHz}$	-	1500	-	pF
Output capacitance	$C_{oss}$		-	131	-	
Reverse transfer capacitance	$C_{rss}$		-	14	-	
Effective output capacitance, energy related <sup>a</sup>	$C_{o(er)}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = 0\text{ V to } 400\text{ V}$	-	113	-	
Effective output capacitance, time related <sup>b</sup>	$C_{o(tr)}$		-	164	-	
Total gate charge	$Q_g$	$V_{GS} = 10\text{ V}$ , $I_D = 9\text{ A}$ , $V_{DS} = 400\text{ V}$	-	38	76	nC
Gate-source charge	$Q_{gs}$		-	11	-	
Gate-drain charge	$Q_{gd}$		-	17	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 400\text{ V}$ , $I_D = 9\text{ A}$ , $V_{GS} = 10\text{ V}$ , $R_g = 9.1\text{ }\Omega$	-	19	38	ns
Rise time	$t_r$		-	36	72	
Turn-off delay time	$t_{d(off)}$		-	36	72	
Fall time	$t_f$		-	30	60	
Gate input resistance	$R_g$	$f = 1\text{ MHz}$ , open drain	-	1.7	-	$\Omega$
<b>Drain-Source Body Diode Characteristics</b>						
Continuous source-drain diode current	$I_S$	MOSFET symbol showing the integral reverse P - N junction diode 	-	-	18	A
Pulsed diode forward current	$I_{SM}$		-	-	72	
Diode forward voltage	$V_{SD}$	$T_J = 25\text{ }^{\circ}\text{C}$ , $I_S = 9\text{ A}$ , $V_{GS} = 0\text{ V}$	-	-	1.2	V
Reverse recovery time	$t_{rr}$	$T_J = 25\text{ }^{\circ}\text{C}$ , $I_F = I_S = 9\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_R = 20\text{ V}$	-	354	-	ns
Reverse recovery charge	$Q_{rr}$		-	3.9	-	$\mu\text{C}$
Reverse recovery current	$I_{RRM}$		-	21	-	A

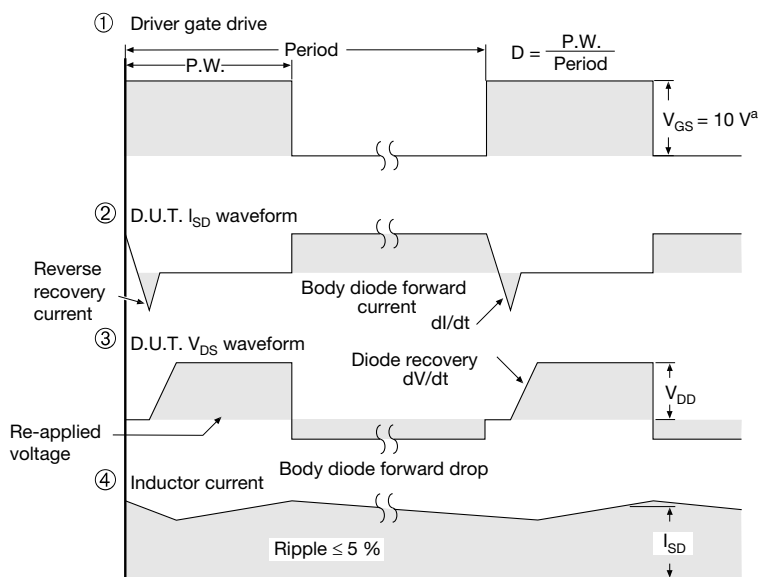
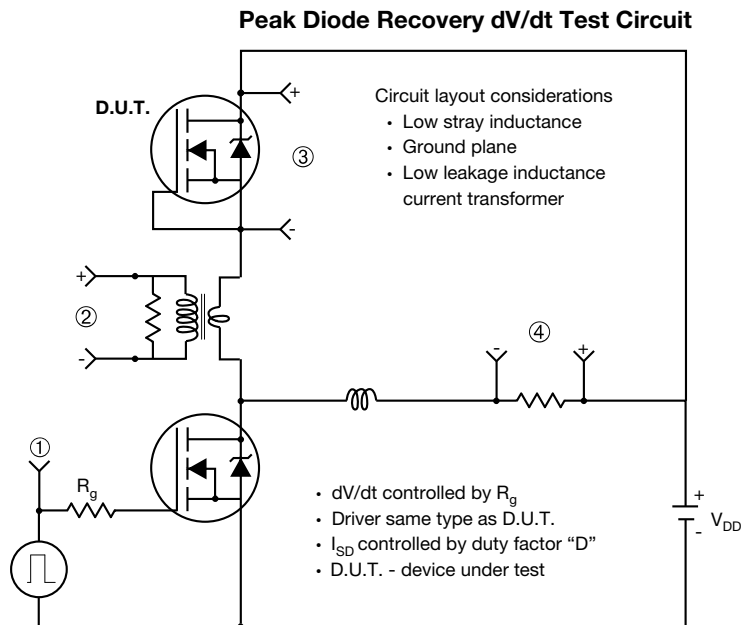
**Notes**

- a.  $C_{oss(er)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$   
b.  $C_{oss(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Fig. 1 - Typical Output Characteristics**

**Fig. 4 - Normalized On-Resistance vs. Temperature**

**Fig. 2 - Typical Output Characteristics**

**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**

**Fig. 3 - Typical Transfer Characteristics**

**Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage**


**Fig. 7 - Typical Source-Drain Diode Forward Voltage**

**Fig. 9 - Maximum Drain Current vs. Case Temperature**

**Fig. 8 - Maximum Safe Operating Area**

**Fig. 10 - Typical Drain-to-Source Voltage vs. Temperature**

**Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case**


**Fig. 12 - Switching Time Test Circuit**

**Fig. 16 - Basic Gate Charge Waveform**

**Fig. 13 - Switching Time Waveforms**

**Fig. 14 - Unclamped Inductive Test Circuit**

**Fig. 15 - Unclamped Inductive Waveforms**

**Fig. 17 - Gate Charge Test Circuit**


**Note**

a.  $V_{GS} = 5 V$  for logic level devices

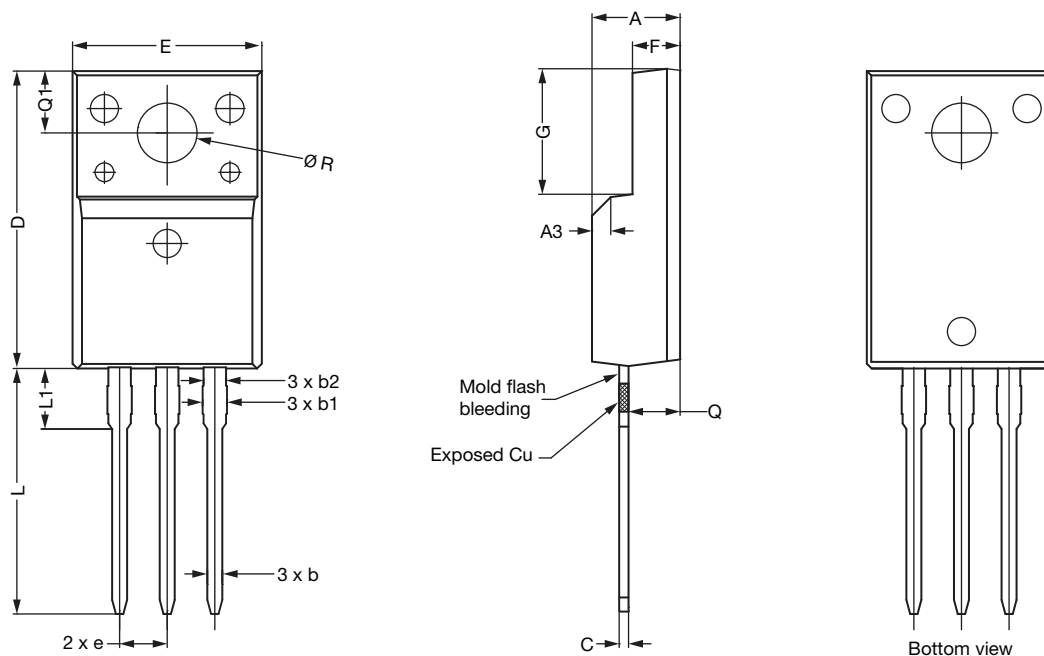
**Fig. 18 - For N-Channel**

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## TO-220 FULLPAK (High Voltage)

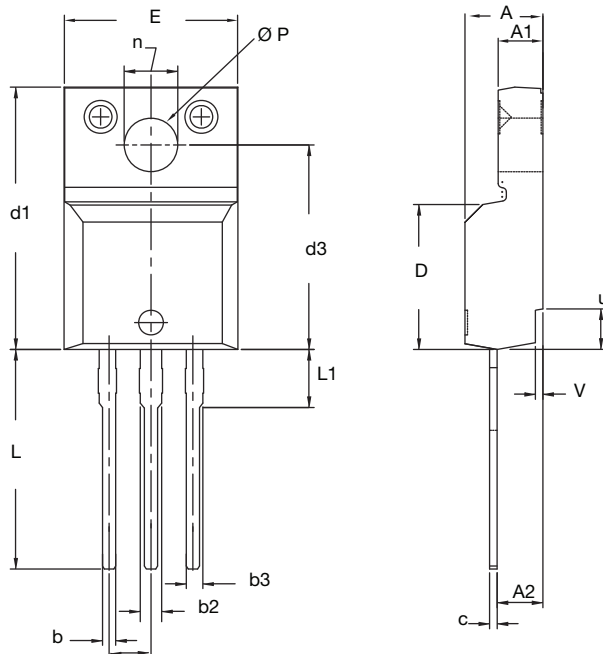
### OPTION 1: FACILITY CODE = 9



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	4.60	4.70	4.80
b	0.70	0.80	0.91
b1	1.20	1.30	1.47
b2	1.10	1.20	1.30
C	0.45	0.50	0.63
D	15.80	15.87	15.97
e	2.54 BSC		
E	10.00	10.10	10.30
F	2.44	2.54	2.64
G	6.50	6.70	6.90
L	12.90	13.10	13.30
L1	3.13	3.23	3.33
Q	2.65	2.75	2.85
Q1	3.20	3.30	3.40
Ø R	3.08	3.18	3.28

#### Notes

1. To be used only for process drawing
2. These dimensions apply to all TO-220 FULLPAK leadframe versions 3 leads
3. All critical dimensions should C meet  $C_{pk} > 1.33$
4. All dimensions include burrs and plating thickness
5. No chipping or package damage
6. Facility code will be the 1<sup>st</sup> character located at the 2<sup>nd</sup> row of the unit marking

**OPTION 2: FACILITY CODE = Y**

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.570	4.830	0.180	0.190
A1	2.570	2.830	0.101	0.111
A2	2.510	2.850	0.099	0.112
b	0.622	0.890	0.024	0.035
b2	1.229	1.400	0.048	0.055
b3	1.229	1.400	0.048	0.055
c	0.440	0.629	0.017	0.025
D	8.650	9.800	0.341	0.386
d1	15.88	16.120	0.622	0.635
d3	12.300	12.920	0.484	0.509
E	10.360	10.630	0.408	0.419
e	2.54 BSC		0.100 BSC	
L	13.200	13.730	0.520	0.541
L1	3.100	3.500	0.122	0.138
n	6.050	6.150	0.238	0.242
Ø P	3.050	3.450	0.120	0.136
u	2.400	2.500	0.094	0.098
V	0.400	0.500	0.016	0.020

ECN: E19-0180-Rev. D, 08-Apr-2019  
DWG: 5972

**Notes**

1. To be used only for process drawing
2. These dimensions apply to all TO-220 FULLPAK leadframe versions 3 leads
3. All critical dimensions should C meet  $C_{pk} > 1.33$
4. All dimensions include burrs and plating thickness
5. No chipping or package damage
6. Facility code will be the 1<sup>st</sup> character located at the 2<sup>nd</sup> row of the unit marking





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